

SuperMOS – TO-252 -30V BV_{DSS}, 8mΩ R_{DS(ON)}, P-channel MOSFET

1. Description

The ESE30P30K is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESE30P30K is Pb-free.

2. Features

- -30V, R_{DS(ON)}=8mΩ(TYP) @V_{GS}=-10V
R_{DS(ON)}=11.5mΩ(TYP) @V_{GS}=-4.5V
 - Fast Switching
 - High density cell design for low R_{DS(on)}
- Material : Halogen free
 - Reliable and rugged
 - Avalanche Rated
 - Low leakage current

3. Applications

- PWM applications
 - Load switch
 - Power management in portable/desktop PCs
 - DC/DC conversion
- 100% UIS TESTED!

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel size
ESE30P30K	TO-252	ESD403/lot	Halogen free	Tape & Reel	2,500 PCS	UL 94V-0	13 inches

Table-1 Ordering information

5. Pin Configuration and Functions

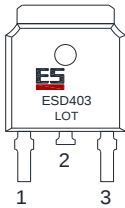
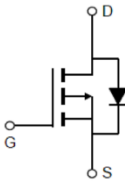
Pin	Function	Outline	Circuit Diagram
1	Gate	Note d 	
3	Source		
2	Drain		

Table-2 Pin configuration

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	-30	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current ^a	$T_C=25^{\circ}C$	I_D	-62	A
	$T_C=75^{\circ}C$		-48	
Maximum Power Dissipation ^a	$T_C=25^{\circ}C$	P_D	79	W
	$T_C=75^{\circ}C$		47	
Pulsed Drain Current ^b		I_{DM}	-200	A
Avalanche Current, Single Pulsed ^c		I_{AS}	-24	A
Avalanche Energy, Single Pulsed ^c		E_{AS}	86.4	mJ
Operating Junction Temperature		T_J	150	°C
Storage Temperature Range		T_{stg}	-55 to +150	°C

Thermal resistance ratings

Single Operation					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ^a	$t \leq 10\text{ s}$	$R_{\theta JA}$	16	20	°C/W
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	0.9	1.6	

Note:

a: Surface mounted on FR4 Board using 1 square inch pad size, 1oz copper

b: Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

c: EAS condition: $T_J=25^{\circ}C$, $V_{DD}=-30V$, $V_G=-10V$, $L=0.3mH$, $R_g=25\Omega$

d: This diagram is only an electrical schematic, and the actual pin size is based on POD.

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±25V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-1	-1.5	-2	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-20A		8	12	mΩ
		V _{GS} =-4.5V, I _D =-20A		11.5	18	
Forward Trans conductance	g _{FS}	V _{DS} =-5.0V, I _D =-20A			80	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, f=1MHz, V _{DS} =15V		2890	3500	pF
Output Capacitance	C _{OSS}			585	760	
Reverse Transfer Capacitance	C _{RSS}			470	660	
Gate Resistance	R _g	f=1MHZ		3.8	5.7	Ω
Total Gate Charge	Q _{G(TOT)}	V _{GS} =-10V, V _{DS} =-15V, I _D =-20A		51	61	nC
Gate-to-Source Charge	Q _{GS}			12	14	
Gate-to-Drain Charge	Q _{GD}			16	22	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =-10V, V _{DS} =-15V, R _L =1Ω, R _G =3Ω		16		ns
Rise Time	t _r			12		
Turn-Off Delay Time	t _{d(OFF)}			45		
Fall Time	t _f			22		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-1.0A		-0.7	-1.5	V

7. Typical Characteristic

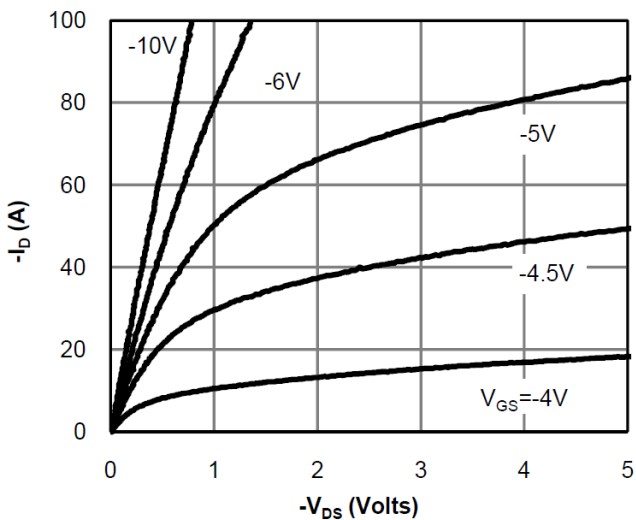


Fig 1: On-Region Characteristics

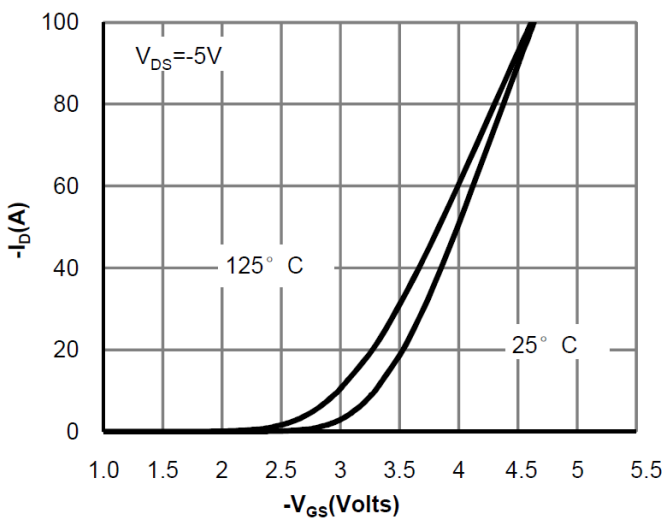


Figure 2: Transfer Characteristics

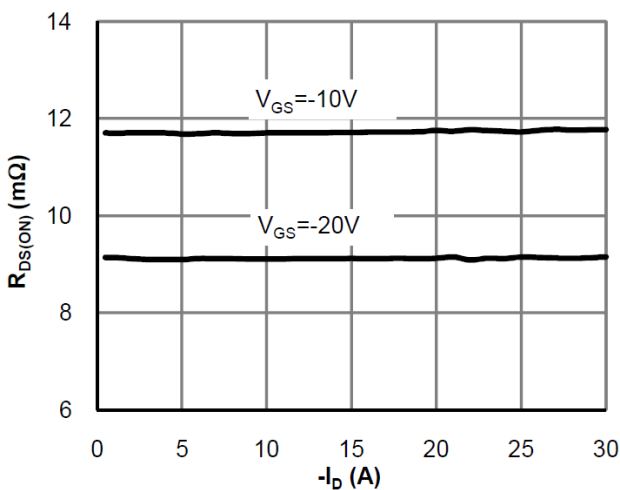


Figure 3: On-Resistance vs. Drain Current and Gate voltage

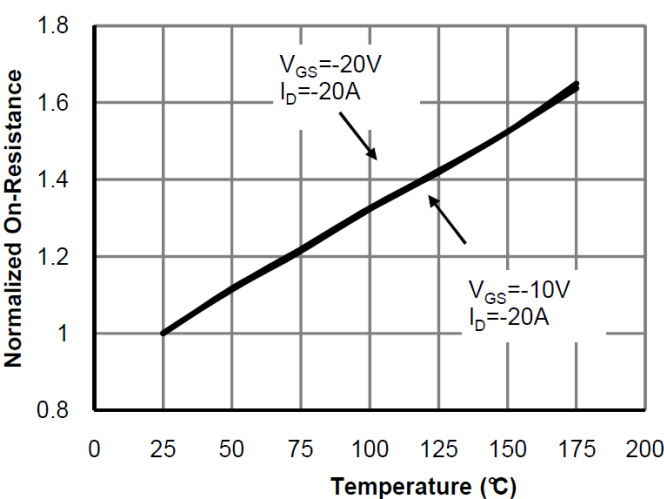


Figure 4: On-Resistance vs. Junction Temperature

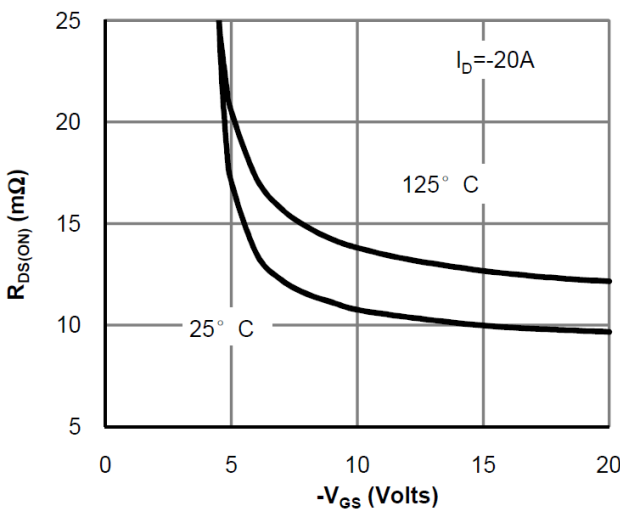


Figure 5: On-Resistance vs. Gate-Source Voltage

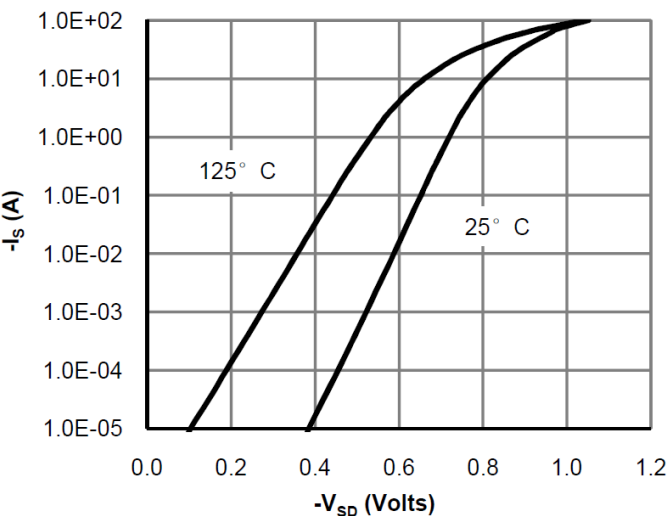


Figure 6: Body-Diode Characteristics

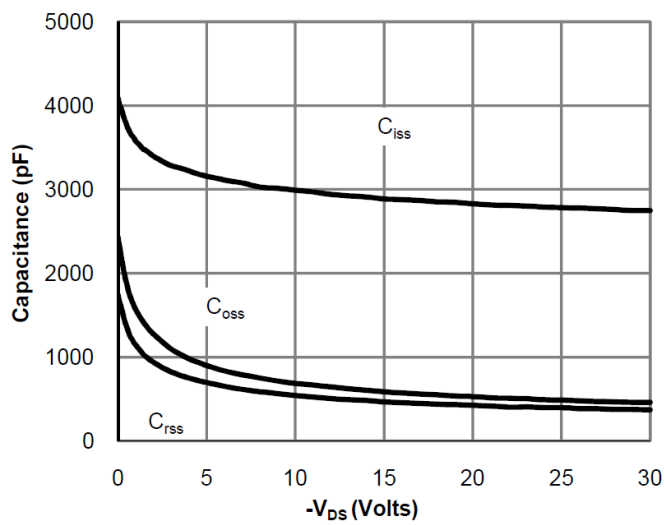
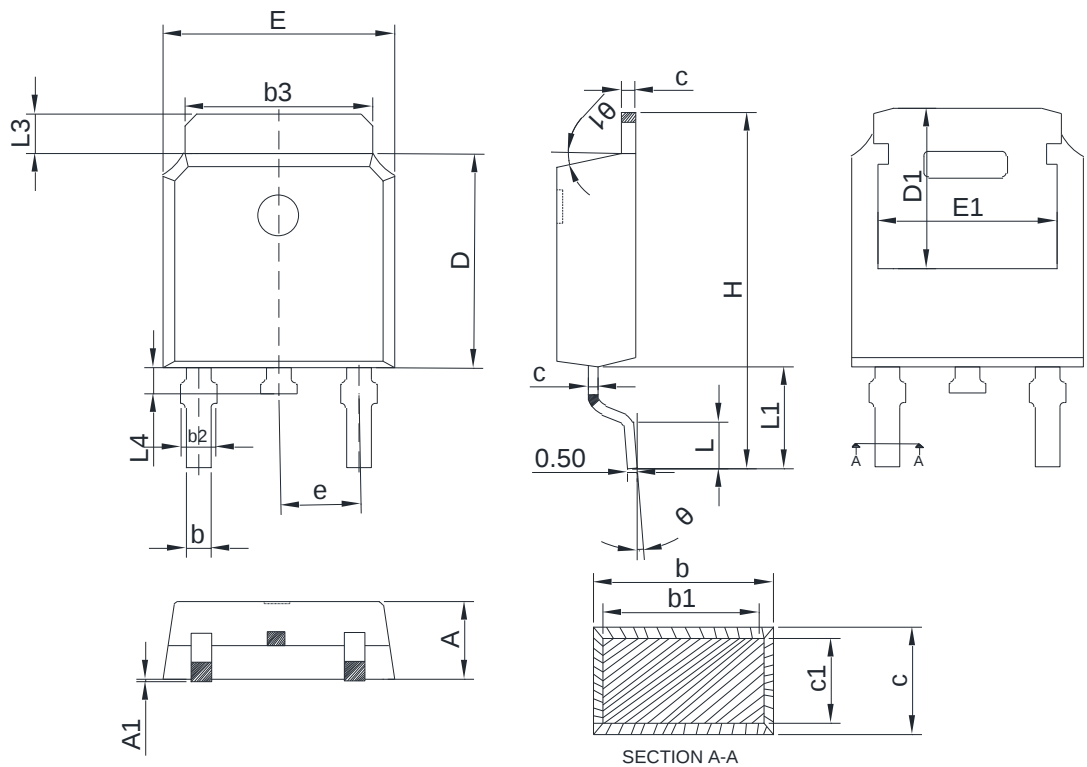


Figure 7: Capacitance Characteristics

8. Dimension (TO-252)

POD A(Q)

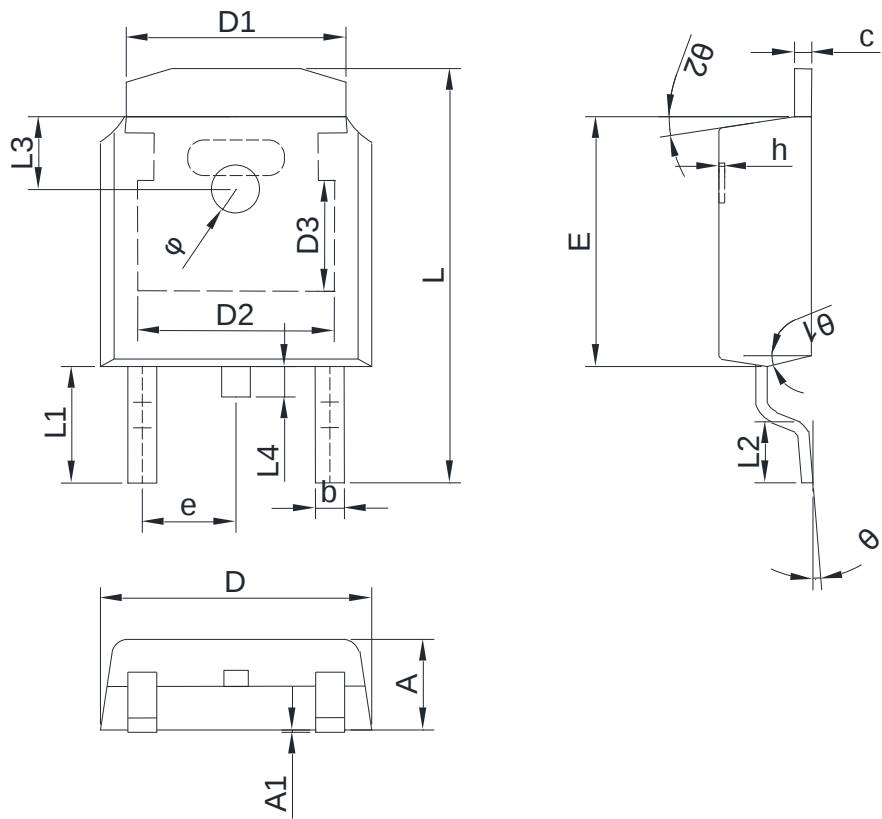


COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER							
SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	2.20	2.30	2.40	D1	5.21	-	-
A1	0.00	-	0.12	E	6.50	6.60	6.70
b	0.65	-	0.89	E1	4.32	-	-
b1	0.64	0.76	0.79	H	9.70	9.95	10.20
b2	0.76	0.86	1.10	L	1.40	1.50	1.60
b3	5.20	5.33	5.46	L1	2.84REF		
c	0.48	-	0.60	e	2.29BSC		
c1	0.47	0.51	0.55	θ	0°	-	10°
D	6.00	6.10	6.20	θ1	0°	-	15°
L3	0.90	-	1.27	L4	0.60	0.80	1.00

ESE30P30K

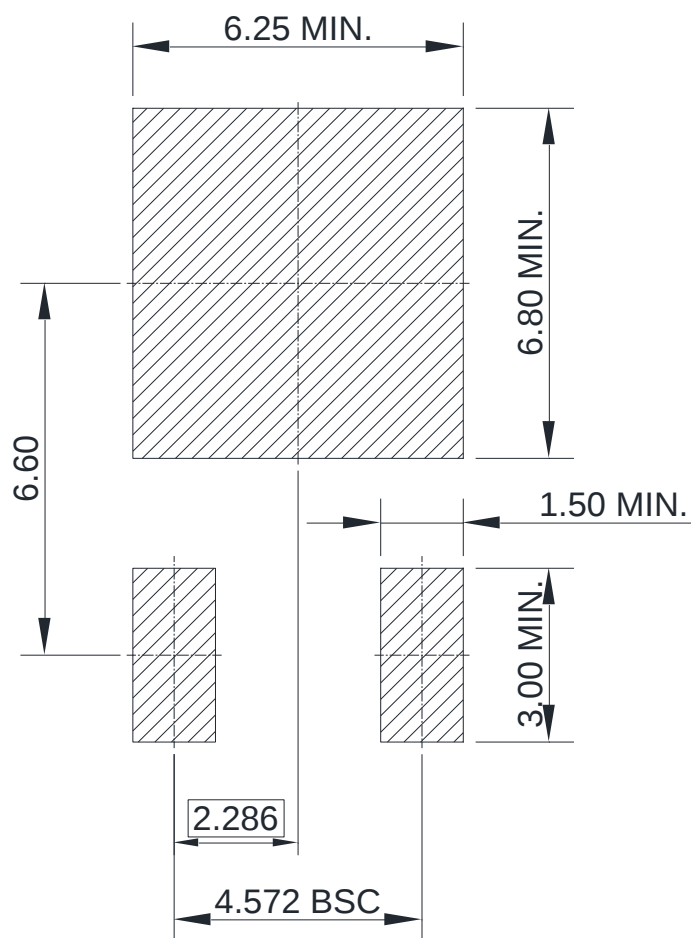
Rev-1.4

POD B(X)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER							
SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	2.200	2.300	2.400	h	0.000	0.100	0.200
A1	0.000		0.127	L	9.900	10.100	10.300
b	0.640	0.690	0.740	L1	2.888 REF		
c(电镀后)	0.460	0.520	0.580	L2	1.400	1.550	1.700
D	6.500	6.600	6.700	L3	1.600 REF		
D1	5.334 REF			L4	0.600	0.800	1.000
D2	4.826 REF			φ	1.100	1.200	1.300
D3	3.166 REF			θ	0°		8°
E	6.000	6.100	6.200	θ1	9° TYP		
e	2.286 TYP			θ2	9° TYP		

9. Recommended Soldering Footprint



DIMENSIONS: MILLIMETERS

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